

Phase Transitions

$$R_S = \frac{V_{max}}{I}$$

$$\text{BaTiO}_3, C = \frac{V_{meas}}{V_0 \omega R_0}$$

$$P \cdot 10^{-12}$$

$$V_0 = 1 \text{ V}$$

$$\omega = 2\pi \text{ kHz}$$

$$R_0 = 1000 \Omega$$

We were only able to get 1 good run for both
 BaTiO_3 and VO_2

$$\text{VO}_2, I = \frac{V}{R} = \frac{1 \text{ V}}{1 \text{ M}\Omega} \text{ according to manual}$$

$$R_S = \frac{V_{meas}}{I} = \frac{V_{max} R_0}{V_0} = V_{max} \times 10^6$$

$$T_c = \frac{1}{2}(T_L + T_H) \quad T^* = \frac{1}{2}(T_c - T_L + T_H - T_c) = \frac{1}{2}(T_H - T_L)$$

$$\bar{T}_{HL} = \left(\frac{T_L}{\sigma_L^2} + \frac{T_H}{\sigma_H^2} \right) \left(\frac{1}{\sigma_L^2} + \frac{1}{\sigma_H^2} \right)^{-1}$$

Area and length approximations for P and A and for C
 Why the large gap in R for VO_2

get value for $P, \sigma_P, C_0, \sigma_{C_0}$

$\text{VO}_2:$

$$\text{diameter} = .8913 \pm .00025 \text{ in.}$$

Semiconducting gap or ground line fit

BaTiO_3

$$\text{width} = 0.3406 \pm .00025 \text{ in.}$$

Rough Errors for BaTiO_3 Capacitance

$$\text{length} = 0.2882 \pm .00025 \text{ in.}$$

$$.00025 \text{ in} = 6.35 \times 10^{-6} \text{ m}$$

look at values that are far out

$$.8913 \text{ in} = 0.0226 \text{ m}$$

$$.3406 \text{ in} = 0.00865 \text{ m}$$

$$.2882 \text{ in} = 0.00732 \text{ m}$$

VO₂

$$P = R \frac{A}{L} \quad - \text{x Sectional Area}$$

length

$$\pi d \cdot \pi r^2$$

$\frac{1}{6}$ mix of Ba
.08

BaTiO₃

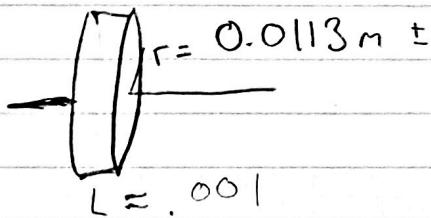
$$C_0 = \epsilon_0 \frac{A}{d} \quad - \text{x Sect. Area}$$

- Separat.

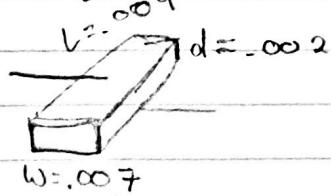
$\frac{1}{13}$ with Ba

0.000006 35

VO₂



BaTiO₃



comptitive?

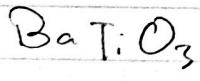
$$V_{O_2} \quad R = V_{bias} \cdot \frac{R_0(1M\Omega)}{V_0 - V}$$

V

Pg^e

- E_g $E_g > 2eV \Rightarrow$ good insulator
- Resistance ratio
- Absolute resistivities
- T_c ✓
- T_{coarse} ✓
- Temp of percolation trans. to T_M

empty capacitors?
Pg 9



$$C = \frac{N_{bias}}{J_0 W R_0} (W)(25\text{kHz}) (100\text{nF})$$

Pg 16

- Relative dielectric constant vs. T

$$K = \frac{C_{0T0}}{C_0}, \quad C_b = C(T_c), \quad C_{0T0} = \frac{C_0 C_b}{C_b - C}$$

Calculate pg 15

Unbiased

- Curie-Weiss law at $T > T_c$ and Curie-Weiss const

C_0 is capacitance of empty capacitor of some geometry

- Microscopic dipole moment p

- The atomic displacement \times responsible for appearance p

VO_b TO DO

- ✓ Error determination
- ✓ χ^2 analysis

- ✓ Find T_c + Error

- ✓ Find T^* + Error

$$K_B = 8.617 \times 10^{-5} \text{ eV/K}$$

eqn 7.

What is E_g - Semiconducting gap
Calculate E_g

$$\text{resistivity } \rho = \rho_0 \exp\left(\frac{E_g}{2k_B T}\right)$$

$\log \rho$ vs. $1/T$

$$\text{Post} - (0.428 \pm .046 \text{ eV}) \quad \text{Post} + (.7eV)$$

$$\rho = R \frac{A}{L} \quad \begin{matrix} A - \text{cross section area} \\ L - \text{length} \end{matrix}$$

$$\rho = R \frac{A}{L} = R_0 \frac{A}{L} \exp\left(\frac{E_g}{2k_B T}\right)$$

- ✓ Calculate "Resistance Ratio"

~~2000~~ Resist at High Temp
Poster (330)

$$\hookrightarrow \ln\left(\frac{R}{R_0}\right) = \frac{E_g}{2k_B} \left(\frac{1}{T}\right)$$

$$\hookrightarrow \ln(R) = \frac{E_g}{2k_B} \left(\frac{1}{T}\right) + \ln(R_0)$$

Absolute Resistivities in

• Semiconducting phase

Poster ($10^6 \Omega$)

• Metallic phase

($10^4 \Omega$)

- ✓ Percolation transition Temp T_M

When it effectively becomes a metal

(Figures also did this for Semiconductors)

~~$$\sigma_{\log(k)}^2 = \left(\frac{\sigma_R}{R}\right)^2$$~~

$$K_B = 8.617 \times 10^{-5} \text{ eV/K}$$

$$\mu(R) = \frac{E_g}{2K_B} \left(\frac{1}{T} \right) + \mu(R_0)$$

$$\text{Slope } (2K_B) = E_g$$

Simple linear regression

$$y = ax + b$$

$$\hat{b} = \bar{y} - \hat{a} \bar{x} \quad \hat{a} = \frac{\sum (x_i - \bar{x})(y_i - \bar{y})}{\sum (x_i - \bar{x})^2}$$

x_1 has 473 x_2 has 536 \uparrow Slope

0 2 3 4 5 6 7 8 9 0 1 2 3 4 5 6

looking for a slope at different temps $y_B = T$

$$\text{Slope at middle index } \hat{a}_{(k+\frac{j-1}{2})} = \frac{\sum_{i=k}^{k+j} (x_i - \bar{x}_M)(y_i - \bar{y}_N)}{\sum_{i=k}^{k+j} (x_i - \bar{x}_M)^2}$$

$$\frac{1}{T} @ \text{middle index} = \bar{x}_M$$

$$\bar{x}_M = \frac{1}{j} \sum_{i=k}^{k+j} x_i$$

$$\text{From } k=0 \rightarrow k=473-j_{\max}$$

$$\text{P}(F) = P(F|R) [P(R)] + P(F|O) [P(O)]$$

V_O_2 Eqns

$T_H, T_L, R(T)$

given or found

$$T_c: \quad T_c = \frac{1}{2} (T_H + T_L) \quad \sigma_{T_c} = \sqrt{\sigma_{T_H}^2 + \sigma_{T_L}^2}$$

$$T^*: \quad T^* = \frac{1}{2} \left([T_H - T_c] + [T_c - T_L] \right) = \frac{1}{2} (T_H - T_L) \quad \sigma_{T^*} = \sigma_{T_c}$$

Absolute resistivities:

$$P = R \frac{A}{L} = \pi R \frac{r^2}{L} \quad \sigma_P^2 = \left(\frac{\pi r^2}{L} \right)^2 \sigma_R^2 + \left(\frac{2\pi r L}{L} \right)^2 \sigma_T^2 + \left(\frac{\pi R r^2}{L^2} \right)^2 \sigma_L^2$$

Semiconductor phase resistance

R_s = Weighted avg of $R(T=\text{low})$ for rising and falling

Metallic

R_M " " $"R(T=\text{High})"$

Resistance ratio:

$$P = \frac{R_s}{R_M} \quad \sigma_P = \sqrt{\left(\frac{\sigma_{R_s}}{R_M} \right)^2 + \left(\frac{R_s \sigma_{R_M}}{R_M^2} \right)^2}$$

Semiconducting gap E_g

$$P = P_0 \exp\left(\frac{E_g}{2k_B T}\right)$$

$$\hookrightarrow R = R_0 \exp\left(\frac{E_g}{2k_B T}\right) \rightarrow \ln(R) = \frac{E_g}{2k_B} \left(\frac{1}{T}\right) + \ln(R_0)$$

See previous page for rolling value

Method 2: look at slopes from $T=40$ to 44 and do weighted Avg

Weighted Avg / Error

$$\sigma_{\bar{x}}^2 = \left(\sum_{n=1}^N \frac{1}{\sigma_n^2} \right)^{-1}$$

$$\bar{x} = \sigma_{\bar{x}}^2 \left(\sum_{n=1}^N \frac{x_n}{\sigma_n^2} \right)$$

$$C_0 = \epsilon_0 \frac{A}{d} = \epsilon_0 \frac{L\omega}{d}$$

$$L = .0087 \pm .0005$$

$$\omega = .0073$$

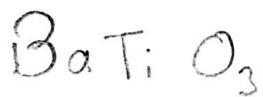
$$d = .002$$

$$\sigma_{C_0}^2 = \epsilon_0^2 \left[\left(\frac{\omega}{d} \right)^2 \sigma_L^2 + \left(\frac{L}{d} \right)^2 \sigma_\omega^2 + \left(\frac{L\omega}{d^2} \right)^2 \sigma_d^2 \right]$$

$\epsilon_0 \approx 10^{-16}$

$$C_o = \epsilon_0 \frac{A}{d}$$

$$\epsilon_0 = 8.85 \times 10^{-12} \frac{F}{N\cdot m}$$



Capacitance of
parallel capacitor

Farads

$$k = \frac{C_{BTO}}{C_o}$$

$$C_n = \frac{1}{\frac{1}{C_b} + \frac{1}{C_{BM}}}$$

@ Phase Transition point $C_b \approx C_M(T_c)$

C_b is independent of temp

$$So \ k(T) = \frac{C_M(T)/C_o}{1 - \left(\frac{C_n(T)}{C_n(T_c)} \right)} = \frac{C_n(T_c) C_M(T)}{C_M(T_c) - C_n(T)} \left(\frac{1}{C_o} \right)$$

$T \neq T_c$

Curie-Weiss Law

Electric Susceptibility $\chi_E = \frac{dP}{dE}$

Near a phase transition $\chi_E \gg 1$ and $T > T_c$

$$\chi_E \approx \frac{C_{CW}}{T - T_c} \quad \text{and} \quad \chi_E \approx \epsilon$$

$$So \ k \approx \frac{C_{CW}}{(T - T_c)}$$

also note

$$\chi_E = \frac{1}{2\alpha(T_c - T)} = \frac{2C_{CW}}{T_c - T} \quad T < T_c$$

$$\chi_E = \frac{1}{4\alpha(T - T_c)} = \frac{C_{CW}}{T - T_c} \quad T > T_c$$

So below T_c , χ_E have factor of 2

$$\text{Plotting } \frac{1}{k} = \frac{1}{C_{CW}}(T - T_c) \quad C_{CW} = \frac{1}{\text{slope}} \quad \sigma_{CW} = \frac{1}{\text{slope}^2} \sigma_{slope}$$

Fix errors with σ_0

$$P = \left(\frac{\epsilon_0 k_B C_{cw}}{N} \right)^{1/2} [C][n] \quad x = \frac{P}{6e}$$

$$N = \frac{1}{a^3} \quad a = 0.4 \text{ nm}$$

$$P = \sqrt{\epsilon_0 k_B a^3} C_{cw}^{1/2}$$

$$\sigma_P = \left(\frac{1}{2} \sqrt{\epsilon_0 k_B a^3} \right)^2 \sigma_{C_{cw}}^2 \quad \sigma_P = \sigma_{C_{cw}} \left(\frac{\epsilon_0 k_B a^3}{4 C_{cw}} \right)^{1/4}$$

$$K(T) = \frac{C_m(T_c) C_n(T)}{C_m(T_c) - C_m(T)} \left(\frac{1}{C_0} \right)$$

$$\sigma_K^2 = \left(\frac{C_m(T)^2}{C_0 (C_m(T_c) - C_m(T))^2} \right)^2 \sigma_C^2 + \left(\frac{C_n(T)^2}{C_0 (C_m(T_c) - C_n(T))^2} \right)^2 \sigma_{C_n}^2 \\ + \left(\frac{C_n(T_c) C_m(T)}{C_0^2 (C_m(T_c) - C_n(T))} \right)^2 \sigma_{C_0}^2$$

$$\frac{1}{K} = \frac{C_n(T_c) - C_m(T)}{C_m(T_c) C_n(T)} \quad C_0 = \frac{C_c - C}{C_c C} C_0$$

plot $\frac{1}{K}$ vs $(T - T_c)$

$$\sigma_{\frac{1}{K}}^2 = \sigma_T^2 + \left(\frac{dy}{dx} \right)^2 \sigma_x^2$$

$$\sigma_{\frac{1}{K}}^2 = \left(\frac{C_c - C}{C_c C} \right)^2 \sigma_{C_0}^2 + \left(\frac{C_0}{C_c^2} \right)^2 \sigma_{C_n}^2 + \left(\frac{C_0}{C^2} \right)^2 \sigma_C^2$$